



HBR3200P

主要参数 MAIN CHARACTERISTICS

$I_{F(AV)}$	3A
V_{RRM}	200 V
T_j	175 °C
$V_{F(max)}$	0.75V (@ $T_j=125^{\circ}C$)

用途

- 低压、高频整流
- 低压续流电路和保护电路

APPLICATIONS

- Low voltage, high frequency rectifier
- Free wheeling diodes, polarity protection applications

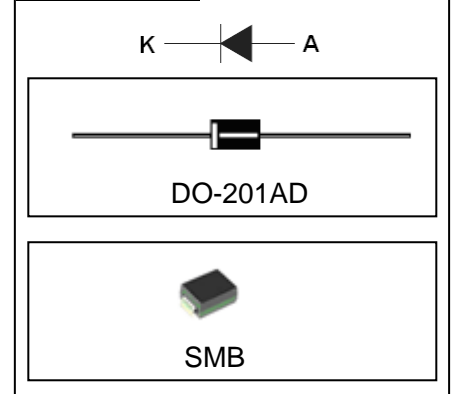
产品特性

- 轴向及贴片结构
- 低功耗，高效率
- 良好的高温特性
- 有过压保护环，高可靠性
- 环保（RoHS）产品

FEATURES

- Axial Lead and Surface Mounting Rectifier
- Low power loss, high efficiency
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability
- RoHS product

封装 Package



订货信息 ORDER MESSAGE

订货型号 Order codes				印 记 Marking	封 装 Package
有卤-条管 Halogen-Tube	无卤-条管 Halogen Free-Tube	有卤-编带 Halogen-Reel	无卤-编带 Halogen Free-Reel		
N/A	N/A	HBR3200P-D-A	HBR3200P-D-AR	HBR3200	DO-201AD
N/A	N/A	HBR3200P-XC-A	HBR3200P-XC-AR	HBR3200	SMB

**绝对最大额定值 ABSOLUTE RATINGS** ($T_c=25^{\circ}\text{C}$)

项 目 Parameter	符 号 Symbol	数 值 Value	单 位 Unit
最大反向重复峰值电压 Repetitive peak reverse voltage	V_{RRM}	200	V
最大直流阻断电压 Maximum DC blocking voltage	V_{DC}	200	V
正向平均整流电流 $T_c=125^{\circ}\text{C}$ Average Rectified Forward Current	$I_{F(AV)}$	3	A
正向峰值浪涌电流 Surge non repetitive forward current (额定负载 8.3ms 半正弦波—按 JEDEC 方法) 8.3 ms single half-sine-wave (JEDEC Method)	I_{FSM}	80	A
最高结温 Maximum junction temperature	T_j	175	$^{\circ}\text{C}$
储存温度 Storage temperature range	T_{STG}	-40~+150	$^{\circ}\text{C}$

电特性 ELECTRICAL CHARACTERISTICS

项 目 Parameter	测试条件 Tests conditions		最小值 Value(min)	典型值 Value(typ)	最大值 Value(max)	单 位 Unit
V_{BR}	$T_j = 25^{\circ}\text{C}$	$I_R = 1\text{mA}$	200			V
I_R	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$			0.1	mA
	$T_j = 125^{\circ}\text{C}$				5	mA
V_F	$T_j = 25^{\circ}\text{C}$	$I_F = 3\text{A}$		0.82	0.92	V
	$T_j = 125^{\circ}\text{C}$			0.72	0.75	V

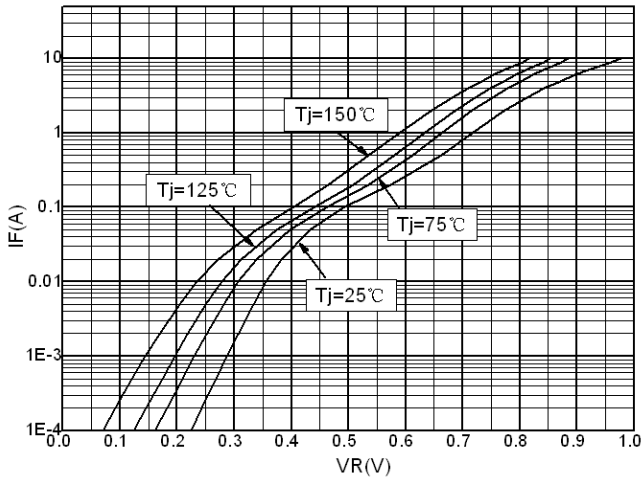
热特性 THERMAL CHARACTERISTICS

项 目 Parameter		符 号 Symbol	最小值 Value(min)	最大值 Value(max)	单 位 Unit
结到环境的热阻 Thermal resistance from junction to ambient	DO-201AD	$R_{th(j-a)}$		70	$^{\circ}\text{C/W}$
	SMB			140	
结到管壳的热阻 Thermal resistance from junction to case	DO-201AD	$R_{th(j-c)}$		25	$^{\circ}\text{C/W}$
	SMB			40	

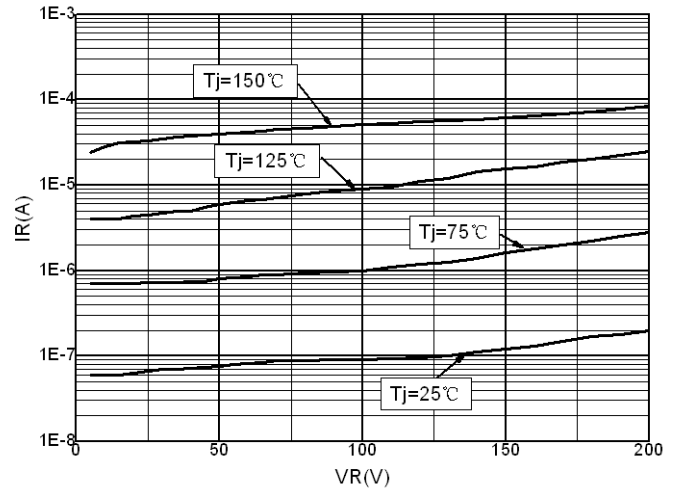


特征曲线 ELECTRICAL CHARACTERISTICS (curves)

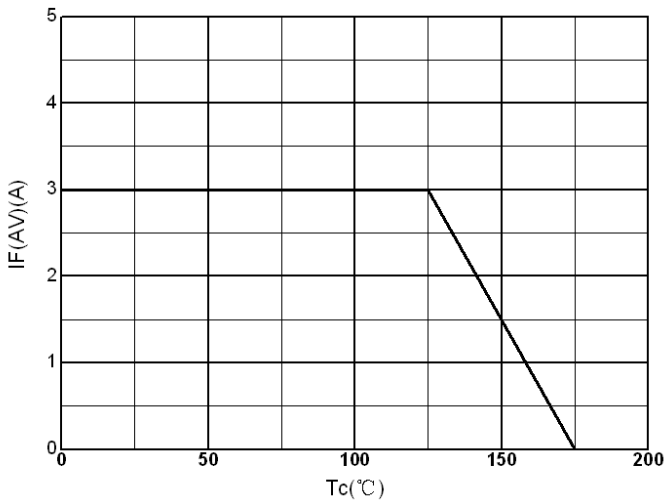
IF vs VF



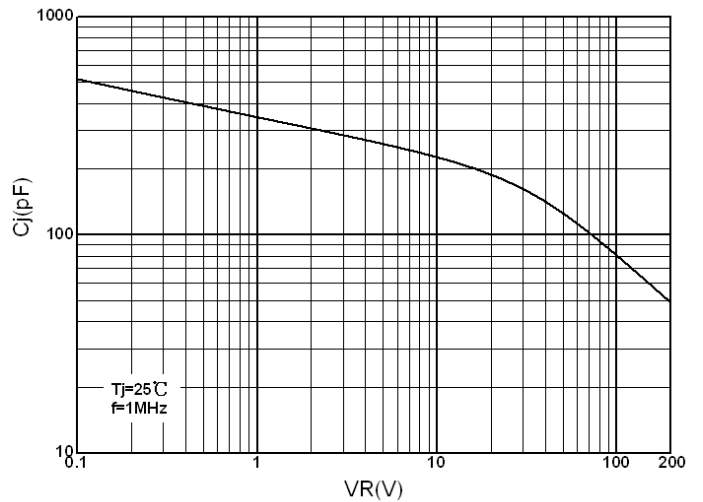
IR vs VR

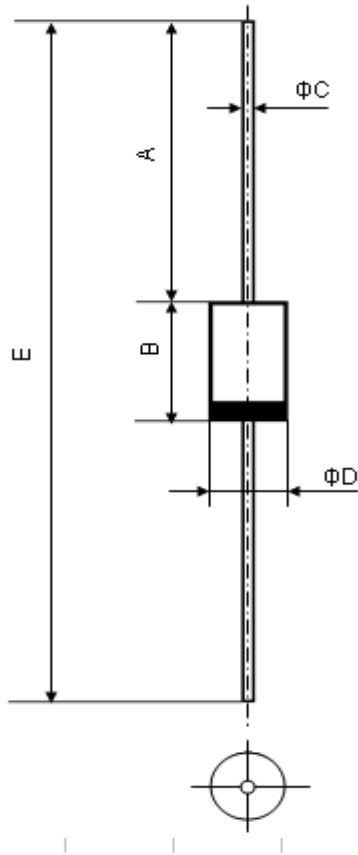


IF(AV) vs Tc

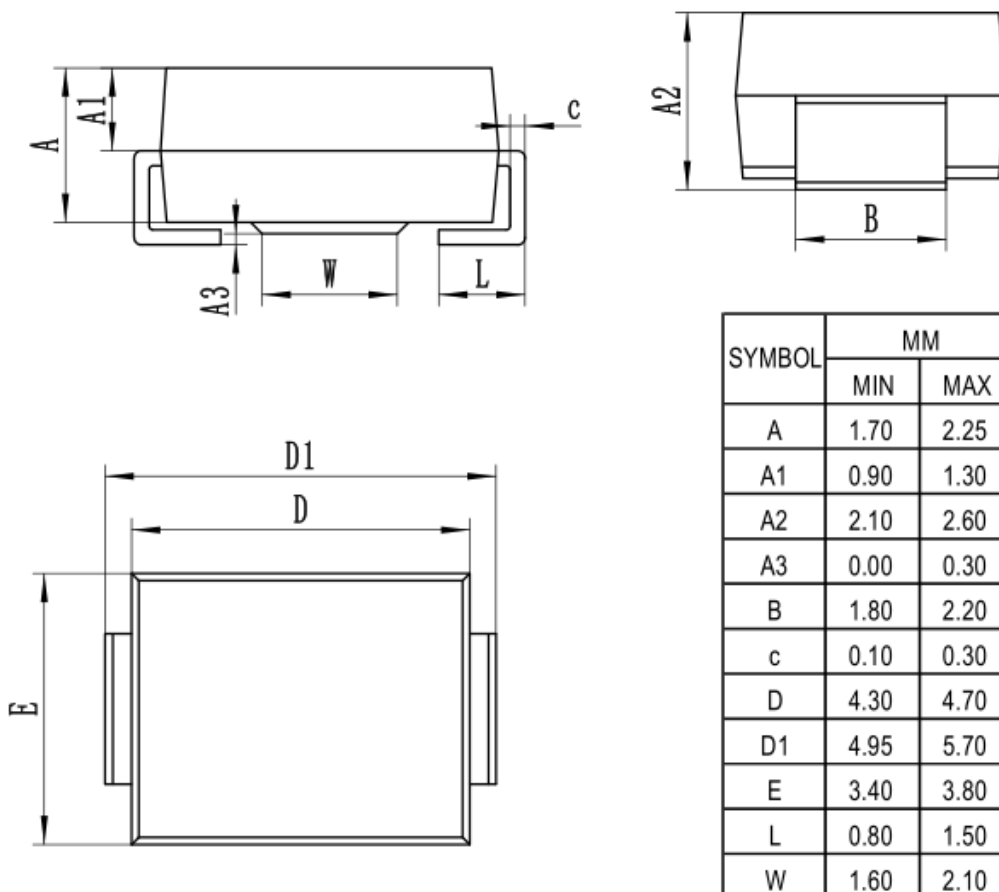


CJ vs VR





符号 Symbol	Min	Max
A	25.4	--
B	8.5	9.5
C	1.2	1.3
D	5.0	5.6
E	59.5	64





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